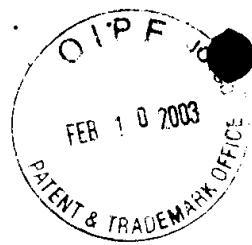


82821



RECEIVED

FEB 11 2003

TC 1700

PATENT

1765
#310
- 1003
(RECEIVED)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re U.S. Patent Application

) Group Art Unit: 1765

)

Applicant: Kozo Nakamura, et al.

) I hereby certify that this correspondence

Serial No.: 09/856,212

) is being deposited with the United States

Filed: May 18, 2001

) Postal Service as first class mail in an

) envelope address to: Assistant

) Commissioner of Patents, Washington, DC

) 20231, on February 4, 2003.

For: Production Method For Silicon Single Crystal

) Gerald T. Shekleton

And Production Device For Single Crystal

) Gerald T. Shekleton Reg. No. 27,466 Date

Ingot, And Heat Treating Method For Silicon

)

Single Crystal Water

Examiner: Matthew J. Song

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

The Office Action of November 5, 2002 has been carefully reviewed and the following
amendments/remarks are made in response thereto.

IN THE CLAIMS

Please amend Claims 1-5, 7 and 9-11 as follows:

1. (Amended) A method for producing a relatively defect free silicon single crystal
ingot under the following conditions: